

Silicon NPN Power Transistors

2SC2660 2SC2660A

DESCRIPTION

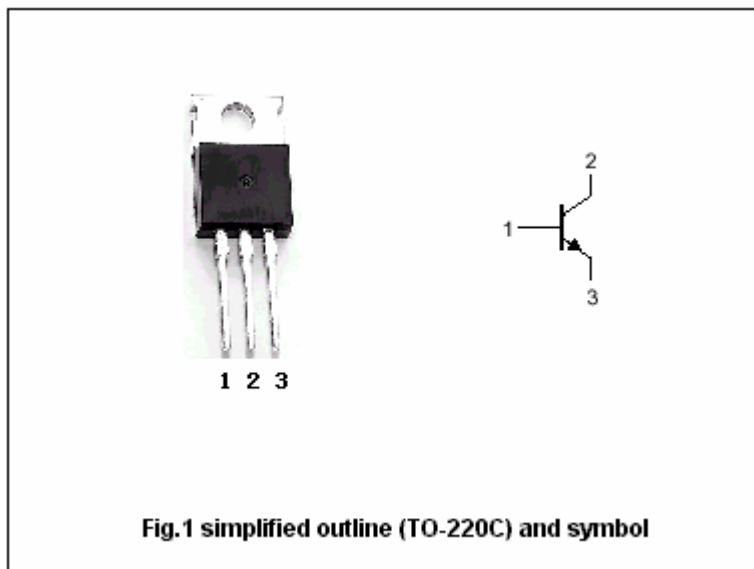
- With TO-220 package
- Complement to type 2SA1133/1133A
- High V_{CEO}
- Large P_C

APPLICATIONS

- Power amplifier applications
- TV vertical deflection applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings ($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage		Open emitter	200	V
V_{CEO}	Collector-emitter voltage	2SC2660	Open base	150	V
		2SC2660A		180	
V_{EBO}	Emitter-base voltage		Open collector	6	V
I_C	Collector current			2	A
I_{CM}	Collector current-peak			3	A
P_C	Collector power dissipation		$T_C=25$	30	W
T_j	Junction temperature			150	
T_{stg}	Storage temperature			-55~150	

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V_{CEsat}	Collector-emitter saturation voltage		$I_C=0.5A ; I_B=50mA$			1.0	V
V_{BE}	Base-emitter on voltage		$I_C=0.4A ; V_{CE}=10V$			1.0	V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	2SC2660	$I_C=5mA ; I_B=0$	150			V
		2SC2660A		180			
$V_{(BR)CBO}$	Collector-base breakdown voltage		$I_C=0.5mA ; I_E=0$	200			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage		$I_E=0.5mA ; I_C=0$	6			V
I_{CBO}	Collector cut-off current		$V_{CB}=200V ; I_E=0$			50	μA
I_{EBO}	Emitter cut-off current		$V_{EB}=4V ; I_C=0$			50	μA
h_{FE-1}	DC current gain		$I_C=0.15A ; V_{CE}=10V$	60		240	
h_{FE-2}	DC current gain		$I_C=0.4A ; V_{CE}=10V$	50			

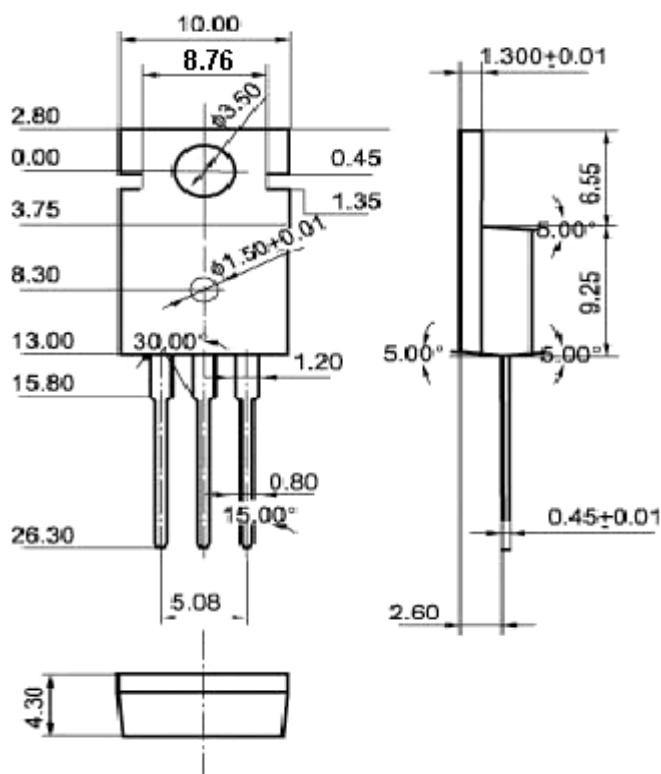
◆ h_{FE-1} classifications

Q	P
60-140	100-240

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PACKAGE OUTLINE

Fig.2 outline dimensions (unindicated tolerance: ± 0.10 mm)